MOSFET – Power, Dual, N-Channel, for 1-2 Cells Lithium-ion Battery Protection 24 V, 2.95 m Ω , 25 A

Introduction

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-2 cells lithium-ion battery applications.

Features

- 2.5 V Drive
- 2 kV ESD HBM
- Common-Drain Type
- ESD Diode-Protected Gate
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

Applications

• 1-2 Cells Lithium-ion Battery Charging and Discharging Switch

Specifications

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C) (Note 1)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V _{SSS}	24	V
Gate to Source Voltage	V _{GSS}	±12	V
Source Current (DC)	۱ _S	25	А
Source Current (Pulse) PW \leq 10 μ s, duty cycle \leq 1%	I _{SP}	100	A
Total Dissipation (Note 1)	PT	2.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	$R_{\theta JA}$	50	°C/W

1. Surface mounted on ceramic substrate (5000 mm² \times 0.8 mm).

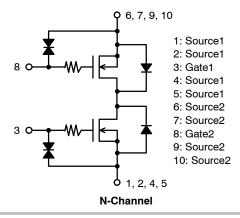


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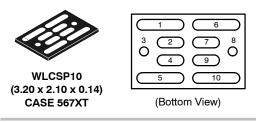
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V _{SSS}	R _{SS(ON)} MAX	I _S MAX
24 V	2.95 mΩ @ 4.5 V	25 A
	3.0 mΩ @ 3.8 V	
	4.7 mΩ @ 3.1 V	
	7.4 mΩ @ 2.5 V	

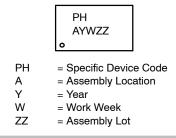
ELECTRICAL CONNECTION



PIN ASSIGNMENT



MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Source to Source Breakdown Voltage	V _{(BR)SSS}	I _S = 1 mA, V _{GS} = 0 V	24			V
Zero-Gate Voltage Source Current	I _{SSS}	V_{SS} = 19.2 V, V_{GS} = 0 V			1	μΑ
Gate to Source Leakage Current	I _{GSS}	$V_{GS} = \pm 8 \text{ V}, \text{V}_{SS} = 0 \text{ V}$			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{SS} = 10 V, I _S = 1 mA	0.4		1.3	V
Static Source to Source On-State Resistance	R _{SS} (on)	I _S = 5 A, V _{GS} = 4.5 V	1.6	2.4	2.95	mΩ
		I _S = 5 A, V _{GS} = 3.8 V	1.7	2.5	3.0	mΩ
		I _S = 5 A, V _{GS} = 3.1 V	2.0	2.9	4.7	mΩ
		I _S = 5 A, V _{GS} = 2.5 V	2.2	3.6	7.4	mΩ
Gate Resistance	Rg	f = 1 MHz		310		Ω
Total Gate Charge	Qg	V_{SS} = 11.5 V, V_{GS} = 4.5 V, I_{S} = 5 A		49		nC
Turn-ON Delay Time	t _d (on)	V_{SS} = 11.5 V, V_{GS} = 4.5 V, R_L = 2.3 Ω		0.6		μs
Rise Time	t _r	$R_G = 0 \Omega$ Switching Test Circuit		1.6		μs
Turn-OFF Delay Time	t _d (off)	1 1		7.3		μs
Fall Time	t _f	1 1		3.2		μs
Forward Source to Source Voltage	V _{F(S-S)}	I _S = 3 A, V _{GS} = 0 V		0.75	1.2	V

ELECTRICAL CHARACTERISTICS (T_A = 25° C)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

SWITCHING TEST CIRCUIT

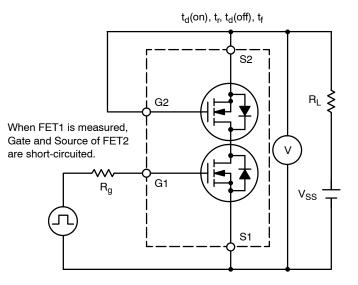


Figure 1. Switching Test Circuit

DEPENDENCY FIGURES

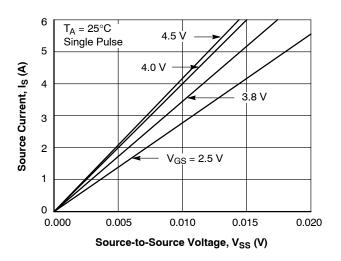


Figure 2. On-Region Characteristics

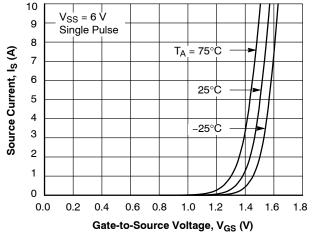


Figure 3. Transfer Characteristics

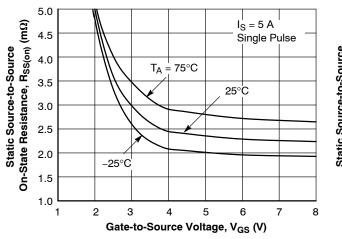


Figure 4. On-Resistance vs. Gate-to-Source Voltage

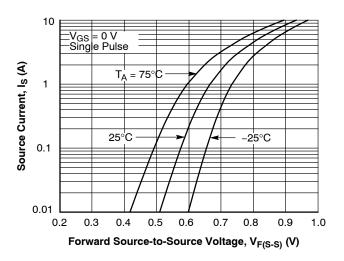


Figure 6. Forward Source-to-Source Voltage vs. Current

5.5 $I_{S} = 5 \text{ Å}$ Static Source-to-Source On-State Resistance, $R_{SS(on)}~(m\Omega)$ 5.0 Single Pulse V_{GS} = 2.5 V 4.5 3.1 V 4.0 3.5 3.0 3.8 V 2.5 4.5 V 2.0 1.5 1.0 40 60 80 100 120 140 160 -60 -40 -20 0 20 Ambient Temperature, T_A (°C)

Figure 5. On-Resistance vs. Temperature

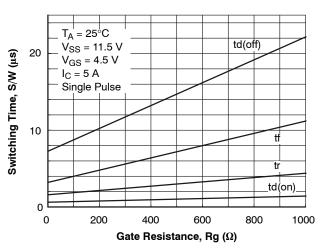


Figure 7. Switching Time vs. Gate Resistance (1)

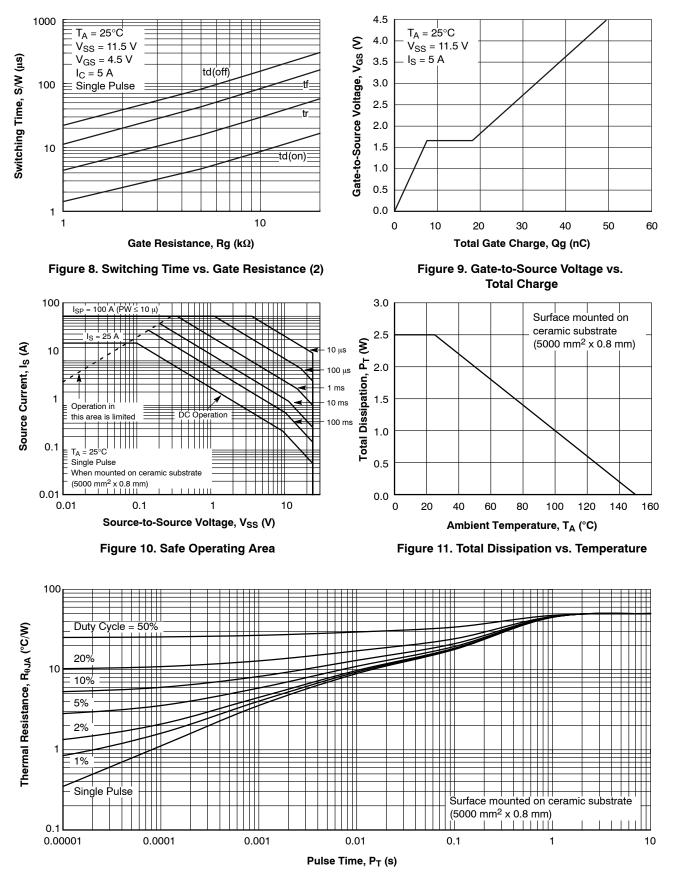


Figure 12. Thermal Response

ORDERING INFORMATION

Device	Marking	Package	Shipping † (Qty / Packing)
EFC4K110NUZTDG	PH	WLCSP10, 3.20 x 2.10 x 0.14 (Pb-Free / Halogen Free)	5000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

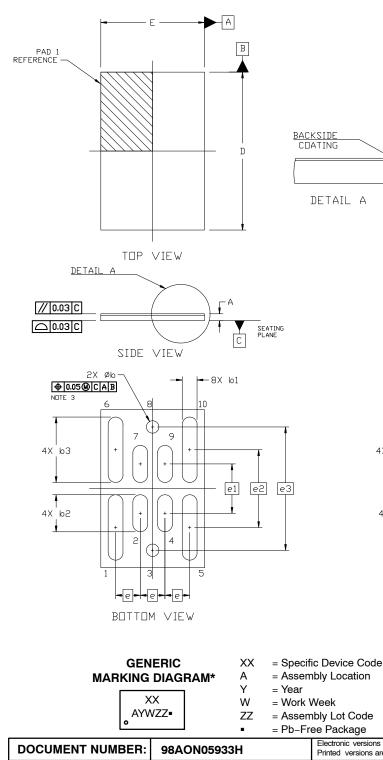
Note on usage: Since the EFC4K110NUZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.



WLCSP10 3.2x2.1x0.14 CASE 567XT

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DATE 02 APR 2019

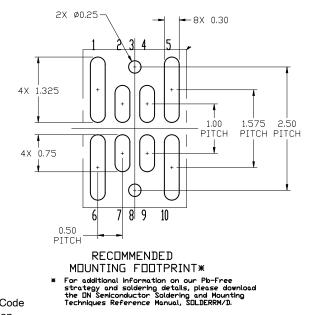


NDTES

L A3

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. POSITIONAL TOLERANCE APPLIES TO ALL PADS.

	MILLIMETERS		
DIM	MIN.	NDM.	MAX.
Α	0.11	0.14	0.17
A3	0.04 REF		
Q	0.22	0.25	0.28
b1	0.27	0.30	0.33
b2	0.72	0.75	0.78
b3	1.295	1.325	1.355
D	3.17	3.20	3,23
E	2.07	2.10	2.13
e	0.50 BSC 1.0 BSC 1.575 BSC 2.50 BSC		
e1			
e2			
e3			



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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 DESCRIPTION:
 WLCSP10 3.2x2.1x0.14
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